



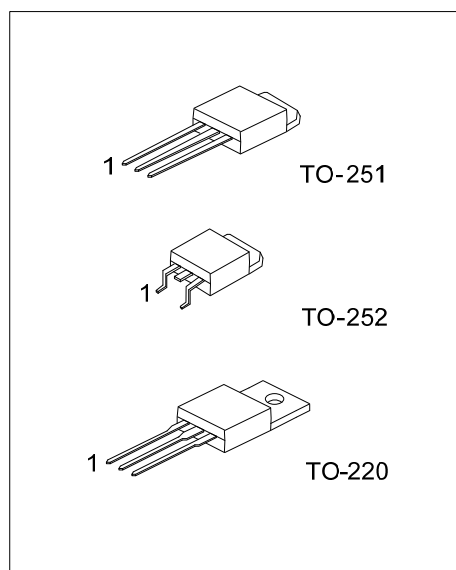
MJE3055T

NPN SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

The UTC **MJE3055T** is designed for general purpose of amplifier and switching applications.



Lead-free: MJE3055TL

Halogen-free: MJE3055TG

ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
MJE3055T-TA3-T	MJE3055TL-TA3-T	MJE3055TG-TA3-T	TO-220	B	C	E	Tube
MJE3055T-TM3-T	MJE3055TL-TM3-T	MJE3055TG-TM3-T	TO-251	B	C	E	Tube
MJE3055T-TN3-R	MJE3055TL-TN3-R	MJE3055TG-TN3-R	TO-252	B	C	E	Tape Reel

MJE3055TL-TA3-T (1)Packing Type (2)Package Type (3)Lead Plating		(1) R: Tape Reel, T: Tube (2) TA3: TO-220, TM3: TO-251, TN3: TO-252 (3)G: Halogen Free, L: Lead Free, Blank: Pb/Sn
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	70	V
Collector-Emitter Voltage		V_{CEO}	60	V
Emitter-Base Voltage		V_{EBO}	5	V
Total Power Dissipation	TO-220	P_D	75	W
	TO-251/TO-252		20	W
Collector Current		I_C	10	A
Base Current		I_B	6	A
Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=200\text{mA}$	60			V
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=10\text{mA}$	70			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=10\text{mA}$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=70\text{V}$			1	mA
	I_{CEO}	$V_{CE}=30\text{V}$			700	μA
	I_{CEX}	$V_{CE}=70\text{V}$, $V_{EB(OFF)}=1.5\text{V}$			1	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5\text{V}$			5	mA
Collector-Emitter Saturation Voltage (Note)	$V_{CE(SAT)1}$	$I_C=4\text{A}$, $I_B=0.4\text{A}$			1.1	V
	$V_{CE(SAT)2}$	$I_C=10\text{A}$, $I_B=3.3\text{A}$			8	V
Base-Emitter on Voltage	$V_{BE(ON)}$	$V_{CE}=4\text{V}$, $I_C=4\text{A}$			1.8	V
DC Current Gain (Note)	h_{FE1}	$V_{CE}=4\text{V}$, $I_C=4\text{A}$	20		100	
	h_{FE2}	$V_{CE}=4\text{V}$, $I_C=10\text{A}$	5			
Current Gain Bandwidth Product	f_T	$V_{CE}=10\text{V}$, $I_C=0.5\text{A}$, $f=1\text{MHz}$	2			MHZ

Note: Pulse test: $PW \leq 300\mu\text{s}$, duty cycle $\leq 2\%$ Pulse

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